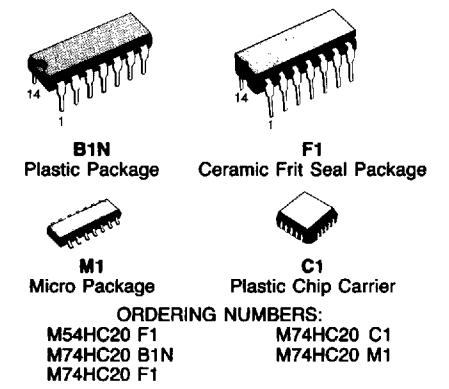



**M54HC20
M74HC20**
S G S - THOMSON
**T-43-21
DUAL 4-INPUT NAND GATE**

- HIGH SPEED
 $t_{PD} = 10 \text{ ns (TYP.)}$ at $V_{CC} = 5\text{V}$
- LOW POWER DISSIPATION
 $I_{CC} = 1 \mu\text{A}$ (MAX.) at $T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY
 $V_{NIH} = V_{NIL} = 28\%$ V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
 $|I_{OH}| = |I_{OL}| = 4 \text{ mA (MIN.)}$
- BALANCED PROPAGATION DELAYS
 $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
 V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE
WITH 54/74LS20

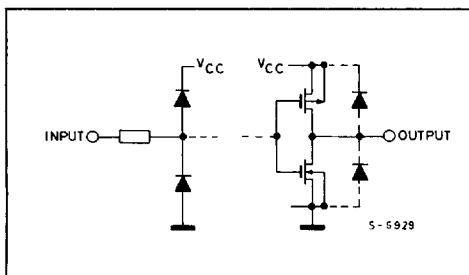


DESCRIPTION

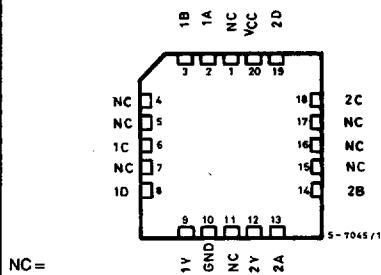
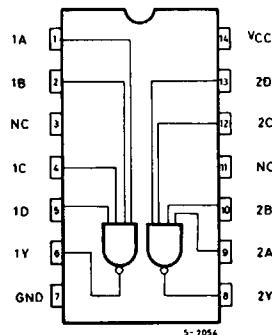
The M54/74HC20 is a high speed CMOS DUAL 4-INPUT NAND GATE fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

The internal circuit is composed of 3 stages including buffered output, which gives high noise immunity and a stable output. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



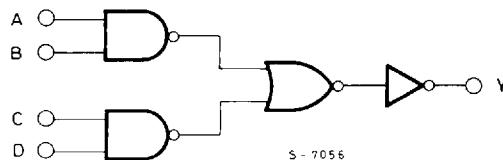
PIN CONNECTIONS (top view)



NC =
No Internal
Connection

S G S-THOMSON

LOGIC DIAGRAM (per Gate)



S - 7056

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to 7	V
V_I	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
V_O	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
Tstg	Storage Temperature	-65 to 150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(*) 500 mW: $\leq 65^\circ\text{C}$ derate to 300 mW by 10 mW/ $^\circ\text{C}$: 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	2 to 6	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_A	Operating Temperature 74HC Series 54HC Series	-40 to 85 -55 to 125	°C
t_r , t_f	Input Rise and Fall Time	V_{CC} { 2 V, 4.5V, 6 V 0 to 1000 ns, 0 to 500 ns, 0 to 400 ns }	ns

DC SPECIFICATIONS

S G S-THOMSON

Symbol	Parameter	V _{CC}	Test Condition	T _A = 25°C 54HC and 74HC			-40 to 85°C 74HC		-55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	2.0 4.5 6.0		1.5 3.15 4.2	— — —	— 3.15 4.2	1.5 3.15 4.2	— — —	1.5 3.15 4.2	— — —	V
V _{IL}	Low Level Input Voltage	2.0 4.5 6.0		— — —	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	V
V _{OH}	High Level Output Voltage	2.0 4.5 6.0	V _I	I _O	1.9 4.4 5.9	2.0 4.5 6.0	— — —	1.9 4.4 5.9	— — —	1.9 4.4 5.9	V
		4.5 6.0	V _{IH} or V _{IL}	— 20 μA — 4.0 mA — 5.2 mA	4.4 5.9 5.68	4.31 5.8	— — —	4.13 5.63	— — —	4.10 5.60	
V _{OL}	Low Level Output Voltage	2.0 4.5 6.0	V _{IH} or V _{IL}	20 μA	— — —	0 0 0.1	— — —	0.1 0.1 0.1	— — —	0.1 0.1 0.1	V
		4.5 6.0		4.0 mA 5.2 mA	— —	0.17 0.18	0.26 0.26	— —	0.33 0.33	— —	0.40 0.40
I _I	Input Leakage Current	6.0	V _I =V _{CC} or GND	— — —	— — —	±0.1	— — —	±1	— — —	±1	μA
I _{CC}	Quiescent Supply Current	6.0	V _I =V _{CC} or GND	— —	— —	1	— —	10	— —	20	μA

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V, T_A = 25°C, C_L = 15pF, Input t_r = t_f = 6ns)

Symbol	Parameter	Test Condition	54HC and 74HC			Unit
			Min.	Typ.	Max.	
t _{TLH} t _{THL}	Output Transition Time		—	4	8	ns
t _{PLH} t _{PHL}	Propagation Delay Time		—	11	18	ns

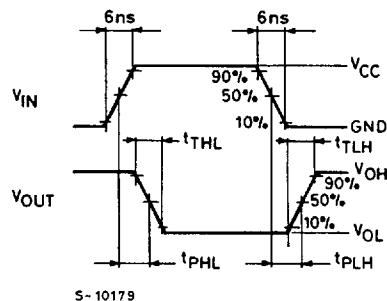
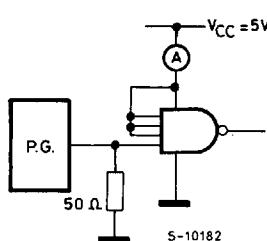
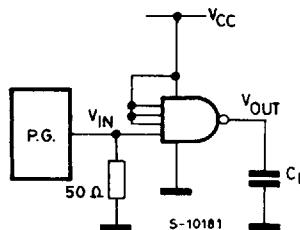
AC ELECTRICAL CHARACTERISTICS (C_L = 50pF, Input t_r = t_f = 6ns)

Symbol	Parameter	V _{CC}	Test Condition	T _A = 25°C 54HC and 74HC			-40 to 85°C 74HC		-55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition Time	2.0 4.5 6.0		— — —	30 8 7	75 15 13	— — —	95 19 16	— — —	110 22 19	ns
t _{PLH} t _{PHL}	Propagation Delay Time	2.0 4.5 6.0		— — —	44 11 9	90 18 15	— — —	115 23 20	— — —	135 27 23	ns
C _{IN}	Input Capacitance			—	5	10	—	10	—	10	pF
C _{PD (*)}	Power Dissipation Capacitance			—	28	—	—	—	—	—	pF

Note (*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit)

SWITCHING CHARACTERISTICS TEST CIRCUIT

S G S-THOMSON

TEST CIRCUIT I_{cc} (Opr.)

INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.